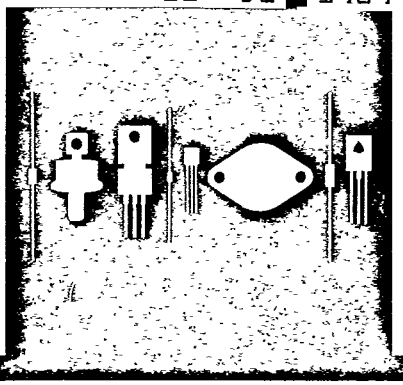
Central Semiconductor Corp.
Central Semiconductor Corp.
Central Semiconductor Corp.
Central™ Semiconductor Corp.
145 Adams Avenue
Hauppauge, New York 11788



CS55AZ
CS55BZ
CS55FZ
CS55DZ
CS55MZ

SCR

0.8 AMPS
50 THRU 600 VOLTS

TO-92-18R CASE

DESCRIPTION

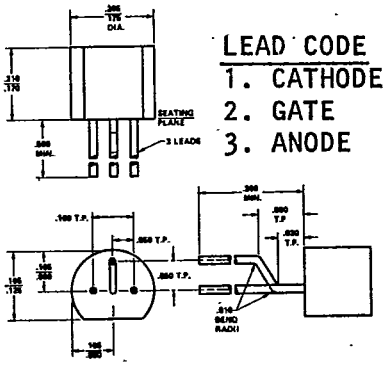
The CENTRAL SEMICONDUCTOR CS55AZ Series is an Epoxy Molded Silicon SCR designed for applications requiring extremely low gate sensitivity.

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	SYMBOL	CS55FZ	CS55AZ	CS55BZ	CS55DZ	CS55MZ	UNIT
Peak Repetitive Off-State Voltage	V_{DRM}	50	100	200	400	600	V
RMS On-State Current	$I_{T(RMS)}$			0.8			A
Peak One Cycle Surge	I_{TSM}			6.0			A
Peak Gate Current	I_{GM}			1.0			A
Average Gate Power Dissipation	$P_{G(AV)}$			0.1			W
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 TO +150			°C
Thermal Resistance	θ_{JA}			180			°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

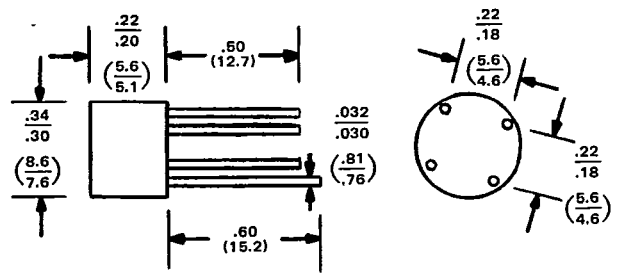
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{DRM}	V_D=Rated V_{DRM}, T_A=125°C			0.05	mA
V_{TM}	I_T=1.0A			1.7	V
I_{GT}	V_D=7.0V, R_L=100Ω			0.02	mA
V_{GT}	V_D=7.0V, R_L=100Ω			0.8	V
I_H	V_D=7.0V, R_{GK}=1.0kΩ			5.0	mA
dv/dt	Exponential Rise to .67 x V_{DRM}, T_A=125°C		50		V/µs
t_{gd}			1.0		µs
t_q			8.0		µs



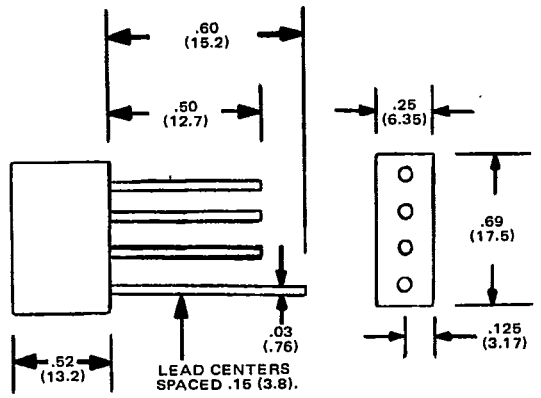
LEAD CODE
1. CATHODE
2. GATE
3. ANODE

CASE OUTLINE DRAWINGS

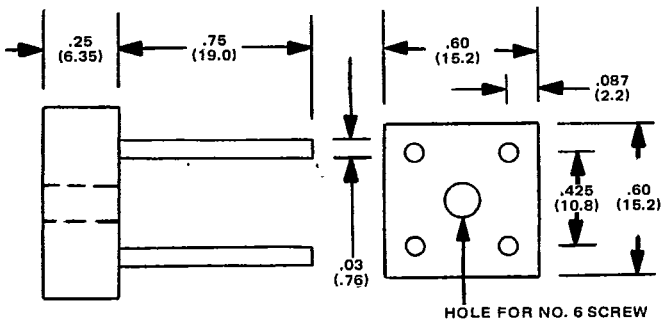
D



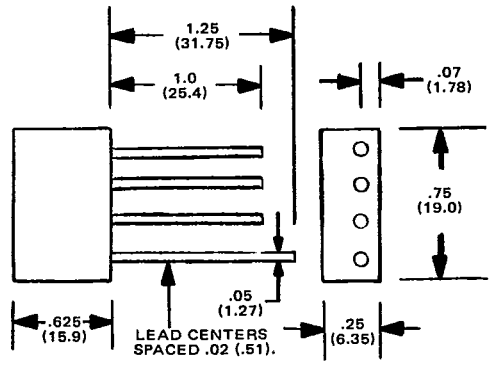
CASE A CBR1 *Series*
CBR2 *Series*



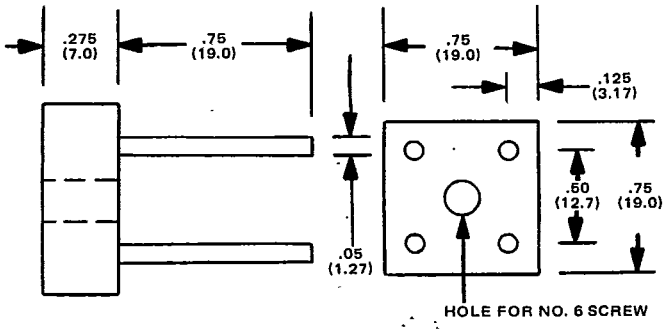
CASE B CBR1-L *Series*
CBR2-L *Series*



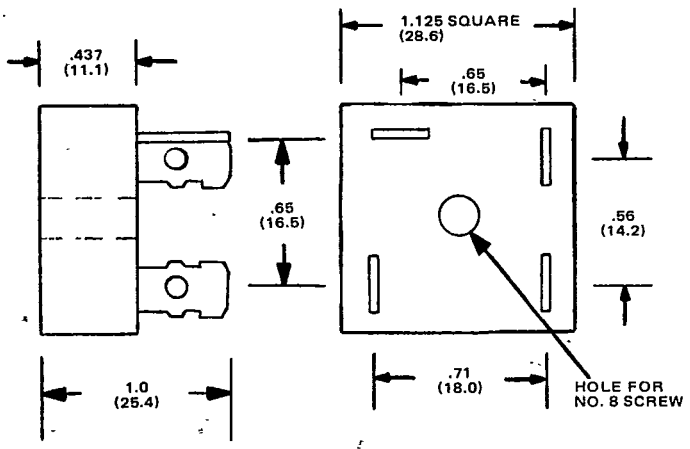
CASE C CBR3-P *Series*



CASE D CBR4-L *Series*



CASE E CBR8 *Series*



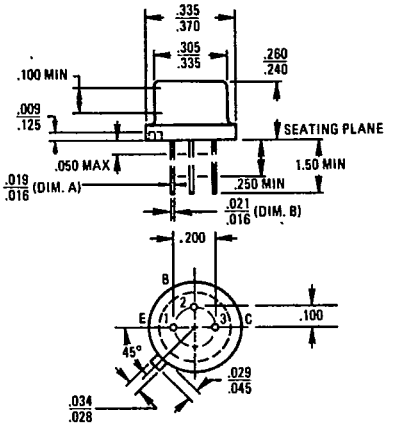
CASE F CBR10 *Series*, CBR25 *Series*
CBR12 *Series*, CBR30 *Series*

All Dimensions in Inches *(Millimeters)*
Drawings Not To Scale

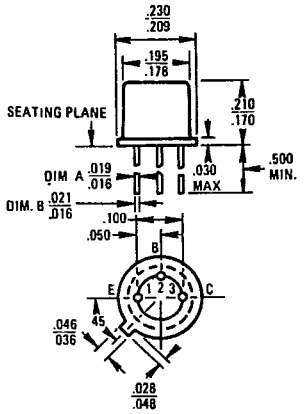
MECHANICAL OUTLINE DRAWINGS

D

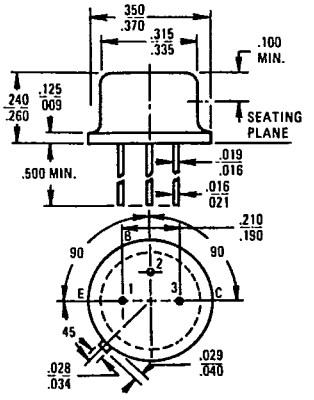
TO-5



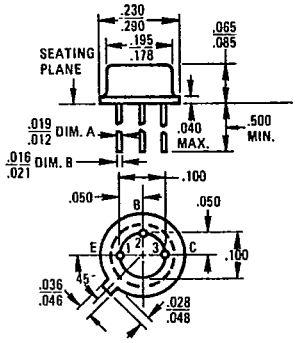
TO-18



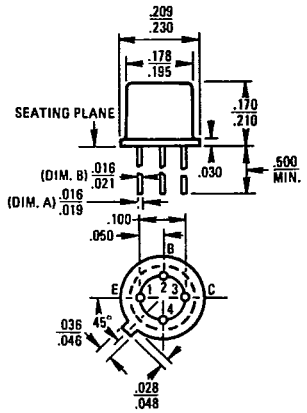
TO-39



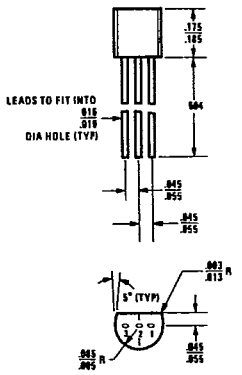
TO-46



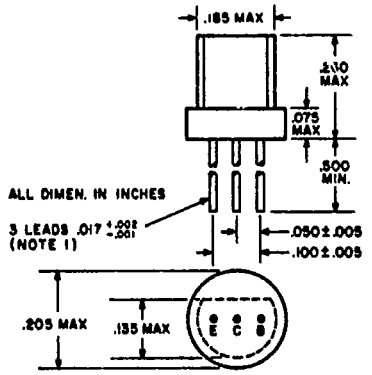
TO-72



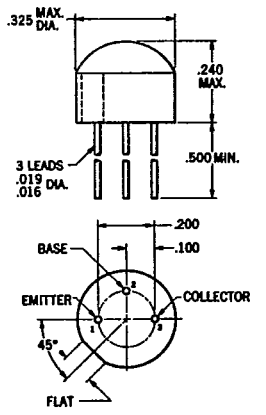
TO-92



TO-98



TO-105



TO-106